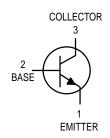
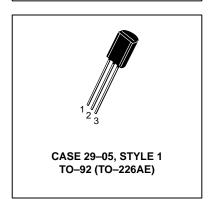
One Watt Amplifier Transistors NPN Silicon

BDB01C,D





MAXIMUM RATINGS

| Rating | Symbol | BDB01C | BDB01D | Unit |
|--|-----------------------------------|-------------|--------|---------------|
| Collector-Emitter Voltage | VCEO | 80 | 100 | Vdc |
| Collector-Base Voltage | VCES | 80 | 100 | Vdc |
| Emitter-Base Voltage | V _{EBO} | 5.0 | | Vdc |
| Collector Current — Continuous | IC | 0.5 | | Adc |
| Total Device Dissipation @ T _A = 25°C Derate above 25°C | PD | 1.0 8.0 | | Watt mW/°C |
| Total Device Dissipation @ T _C = 25°C Derate above 25°C | PD | 2.5 20 | | Watt mW/°C |
| Operating and Storage Junction Temperature Range | T _J , T _{stg} | -55 to +150 | | °C |

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|----------------|-----|------|
| Thermal Resistance, Junction to Ambient | $R_{	heta JA}$ | 125 | °C/W |
| Thermal Resistance, Junction to Case | $R_{	heta JC}$ | 50 | °C/W |

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

| Characteris | stic | Symbol | Min | Max | Unit |
|---|------------------|------------------|-----------|--------------|------|
| OFF CHARACTERISTICS | | | | | |
| Collector-Emitter Voltage (I _C = 10 mA, I _B = 0) | BDB01C BDB01D | V(BR)CEO | 80 100 | | Vdc |
| Collector Cutoff Current $(V_{CB} = 80 \text{ V}, I_{E} = 0)$ $(V_{CB} = 100 \text{ V}, I_{E} = 0)$ | BDB01C BDB01D | ICBO | _ _ | 0.01 0.01 | μAdc |
| Emitter Cutoff Current (I _C = 0, V _{EB} = 5.0 V) | | I _{EBO} | _ | 100 | nAdc |

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

| \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ | , | | | |
|---|---------------------|----------|----------|------|
| Characteristic | Symbol | Min | Max | Unit |
| ON CHARACTERISTICS | | | • | • |
| DC Current Gain (I _C = 100 mA, V _{CE} = 1.0 V) (I _C = 500 mA, V _{CE} = 2.0 V) | hFE | 40 25 | 400 — | _ |
| Collector-Emitter Saturation Voltage ⁽¹⁾ (I _C = 1000 mA, I _B = 100 mA) | VCE(sat) | _ | 0.7 | Vdc |
| Collector-Emitter On Voltage(1) (I _C = 1000 mA, V _{CE} = 1.0 V) | V _{BE(on)} | _ | 1.2 | Vdc |
| DYNAMIC CHARACTERISTICS | | | | |
| Current Gain Bandwidth Product (I _C = 200 mA, V _{CE} = 5.0 V, f = 20 MHz) | fT | 50 | _ | MHz |
| Output Capacitance (V _{CB} = 10 V, I _E = 0, f = 1.0 MHz) | C _{ob} | _ | 30 | pF |

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle 2.0%.

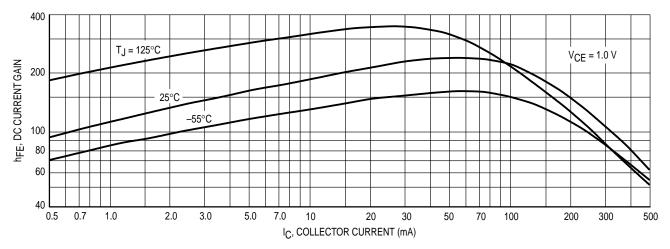


Figure 1. DC Current Gain

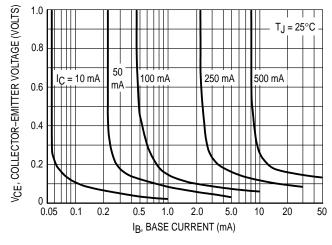


Figure 2. Collector Saturation Region

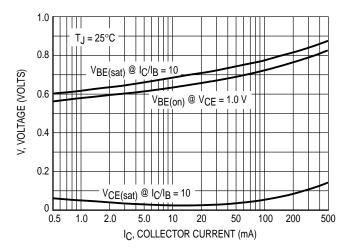


Figure 3. On Voltages

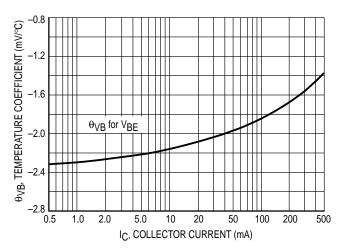
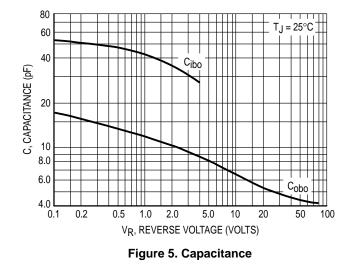


Figure 4. Base–Emitter Temperature Coefficient



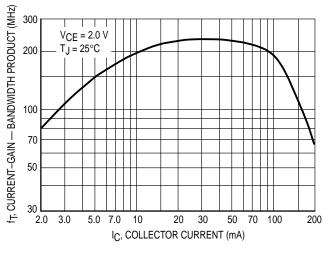


Figure 6. Current-Gain — Bandwidth Product

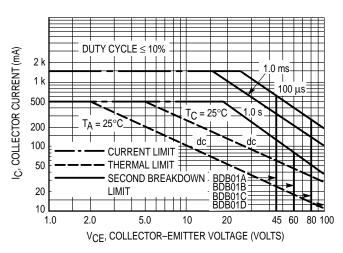
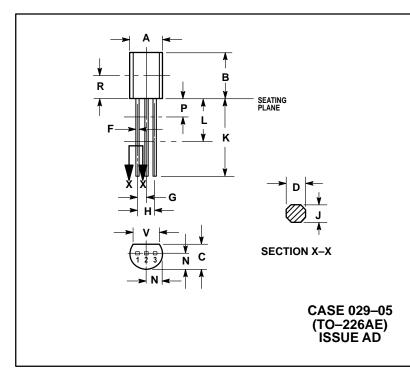


Figure 7. Active Region-Safe Operating Area

PACKAGE DIMENSIONS



- 1. DIMENSIONING AND TOLERANCING PER ANSI
- 714.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- 4. DIMENSION F APPLIES BETWEEN P AND L. DIMENSIONS D AND J APPLY BETWEEN L AND K MIMIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| | INCHES | | MILLIMETERS | | |
|-----|--------|-------|-------------|------|--|
| DIM | MIN | MAX | MIN | MAX | |
| Α | 0.175 | 0.205 | 4.44 | 5.21 | |
| В | 0.290 | 0.310 | 7.37 | 7.87 | |
| C | 0.125 | 0.165 | 3.18 | 4.19 | |
| D | 0.018 | 0.022 | 0.46 | 0.56 | |
| F | 0.016 | 0.019 | 0.41 | 0.48 | |
| G | 0.045 | 0.055 | 1.15 | 1.39 | |
| Н | 0.095 | 0.105 | 2.42 | 2.66 | |
| 7 | 0.018 | 0.024 | 0.46 | 0.61 | |
| K | 0.500 | | 12.70 | | |
| L | 0.250 | | 6.35 | | |
| N | 0.080 | 0.105 | 2.04 | 2.66 | |
| Р | | 0.100 | | 2.54 | |
| R | 0.135 | _ | 3.43 | | |
| V | 0.135 | | 3 43 | | |

STYLE 1: PIN 1. EMITTER 2. BASE 3. COLLECTOR

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